Jean-Baptiste Leran

List of Publications by Year
in descending order

20 papers	269 citations	1163117 8 h-index	940533 16 g-index
20 all docs	20 docs citations	20 times ranked	353 citing authors

#	Article	IF	Citations
1	Nanoscale Growth Initiation as a Pathway to Improve the Earth-Abundant Absorber Zinc Phosphide. ACS Applied Energy Materials, 2022, 5, 5298-5306.	5.1	3
2	Showcasing the optical properties of monocrystalline zinc phosphide thin films as an earth-abundant photovoltaic absorber. Materials Advances, 2022, 3, 1295-1303.	5.4	7
3	GaAs nanowires on Si nanopillars: towards large scale, phase-engineered arrays. Nanoscale Horizons, 2022, 7, 211-219.	8.0	4
4	Nanoscale Mapping of Light Emission in Nanospade-Based InGaAs Quantum Wells Integrated on Si(100): Implications for Dual Light-Emitting Devices. ACS Applied Nano Materials, 2022, 5, 5508-5515.	5.0	0
5	Towards defect-free thin films of the earth-abundant absorber zinc phosphide by nanopatterning. Nanoscale Advances, 2021, 3, 326-332.	4.6	13
6	van der Waals Epitaxy of Co_{10â€“<i>x</i>}Zn_{10â€“<i>y</i>}Mn_{<i>x</i>+<i>y</i>} Thin Films: Chemical Composition Engineering and Magnetic Properties. Journal of Physical Chemistry C, 2021, 125, 9391-9399.	3.1	1
7	The path towards 1 Âµm monocrystalline Zn₃P₂ films on InP: substrate preparation, growth conditions and luminescence properties. JPhys Energy, 2021, 3, 034011.	5.3	8
8	Modeling the Shape Evolution of Selective Area Grown Zn₃P₂ Nanoislands. Crystal Growth and Design, 2021, 21, 4732-4737.	3.0	1
9	Raman spectroscopy and lattice dynamics calculations of tetragonally-structured single crystal zinc phosphide (Zn₃P₂) nanowires. Nanotechnology, 2021, 32, 085704.	2.6	10
10	Rotated domains in selective area epitaxy grown Zn₃P₂: formation mechanism and functionality. Nanoscale, 2021, 13, 18441-18450.	5.6	7
11	Raman tensor of zinc-phosphide (Zn₃P₂): from polarization measurements to simulation of Raman spectra. Physical Chemistry Chemical Physics, 2021, 24, 63-72.	2.8	3
12	Multiple morphologies and functionality of nanowires made from earth-abundant zinc phosphide. Nanoscale Horizons, 2020, 5, 274-282.	8.0	15
13	Heterotwin Zn₃P₂superlattice nanowires: the role of indium insertion in the superlattice formation mechanism and their optical properties. Nanoscale, 2020, 12, 22534-22540.	5.6	7
14	van der Waals Epitaxy of Earth-Abundant Zn₃P₂ on Graphene for Photovoltaics. Crystal Growth and Design, 2020, 20, 3816-3825.	3.0	24
15	IIIâ€“V Integration on Si(100): Vertical Nanospades. ACS Nano, 2019, 13, 5833-5840.	14.6	24
16	Bistability of Contact Angle and Its Role in Achieving Quantum-Thin Self-Assisted GaAs nanowires. Nano Letters, 2018, 18, 49-57.	9.1	62
17	Optimizing the yield of A-polar GaAs nanowires to achieve defect-free zinc blende structure and enhanced optical functionality. Nanoscale, 2018, 10, 17080-17091.	5.6	31
18	Tilting Catalyst-Free InAs Nanowires by 3D-Twinning and Unusual Growth Directions. Crystal Growth and Design, 2017, 17, 3596-3605.	3.0	4

#	Article	IF	Citations
19	Impact of the Ga Droplet Wetting, Morphology, and Pinholes on the Orientation of GaAs Nanowires. Crystal Growth and Design, 2016, 16, 5781-5786.	3.0	38
20	Molecular beam epitaxy of InAs nanowires in SiO2nanotube templates: challenges and prospects for integration of IIIâ€“Vs on Si. Nanotechnology, 2016, 27, 455601.	2.6	7